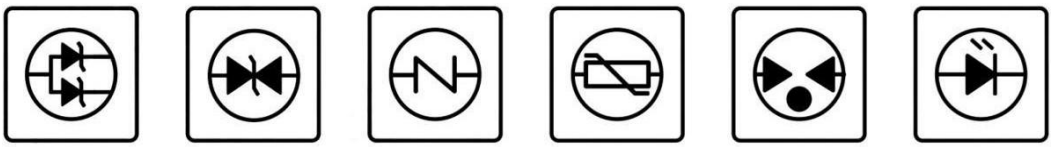
MSKSEMI 美森科
SEMICONDUCTOR



AO4266-MS

Product specification

Description

The AO4266-MS uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

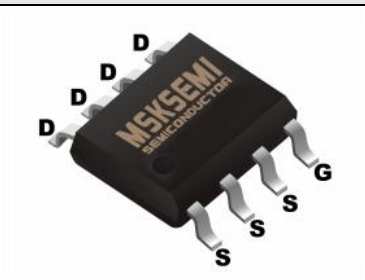
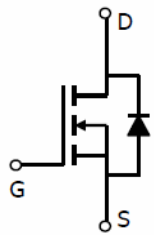
Application

- Power switching application
- Load switch

General Features

- V_{DS} = 60V,I_D =10A
- $R_{DS(ON)}$ < 13mΩ @ V_{GS}=10V (Typ:10mΩ)
- $R_{DS(ON)}$ < 15mΩ @ V_{GS}=4.5V (Typ:11.5mΩ)
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Low gate to drain charge to reduce switching losses

Reference News

PACKAGE OUTLINE	N-Channel MOSFET	Marking
 SOP-8		MSKSEMI 4266 MS**N

Absolute Maximum Ratings (TC=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	10	A
Drain Current-Continuous(T_C=100℃)	I_D (100℃)	8.5	A
Pulsed Drain Current	I_{DM}	30	A
Maximum Power Dissipation	P_D	3	W
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 150	℃

Thermal Characteristic

Thermal Resistance,Junction-to-Ambient (Note 2)	$R_{\theta JA}$	42	℃/W

Electrical Characteristics (TC=25℃unless otherwise noted)

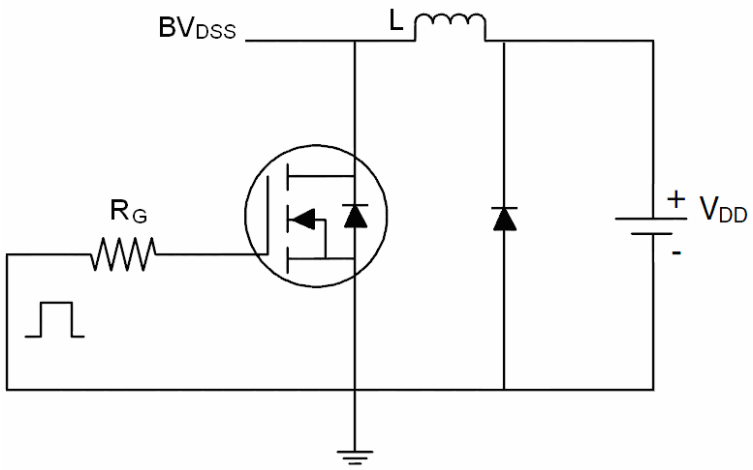
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	60		-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=60V,V_{GS}=0V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS} ,I_D=250μA	0.9	1.3	1.8	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=10A	-	10	13	mΩ
		V_{GS}=4.5V, I_D=5A	-	11.5	15	mΩ
Forward Transconductance	g_{FS}	V_{DS}=5V,I_D=12A	40	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{lss}	V_{DS}=30V,V_{GS}=0V, F=1.0MHz	-	4100	-	PF
Output Capacitance	C_{oss}		-	298	-	PF
Reverse Transfer Capacitance	C_{rss}		-	229	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=30V, R_L=1Ω V_{GS}=10V,R_{GEN}=3Ω	-	8.5	-	nS
Turn-on Rise Time	t_r		-	7	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	40	-	nS
Turn-Off Fall Time	t_f		-	15	-	nS
Total Gate Charge	Q_g	V_{DS}=30V,I_D=10 A, V_{GS}=10V	-	93	-	nC
Gate-Source Charge	Q_{gs}		-	9.7	-	nC
Gate-Drain Charge	Q_{gd}		-	20	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=10A	-	-	1.2	V
Diode Forward Current (Note 2)	I_S		-	-	10	A
Reverse Recovery Time	t_{rr}	T_J = 25°C, I_F=10A di/dt = 100A/μs(Note3)	-	32	-	nS
Reverse Recovery Charge	Qrr		-	45	-	nC

Notes:

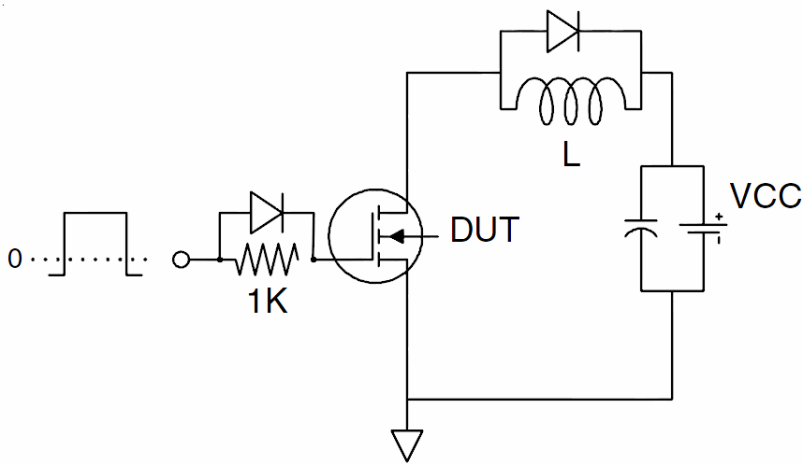
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. The value of RθJA is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with TA =25°C. The value in any given application depends on the user's specific board design.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

Test Circuit

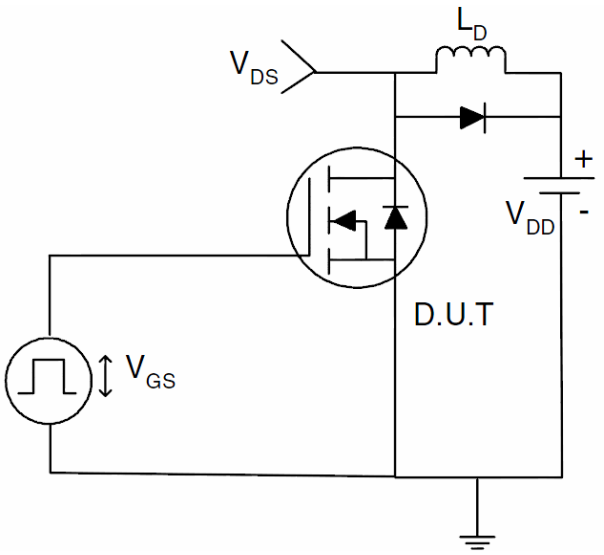
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)

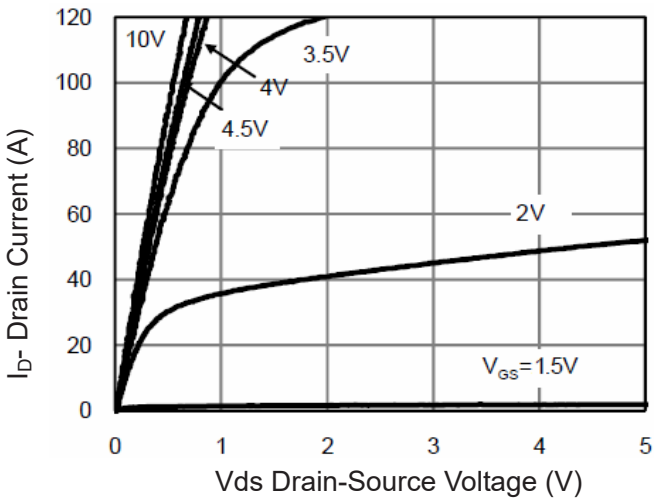


Figure 1 Output Characteristics

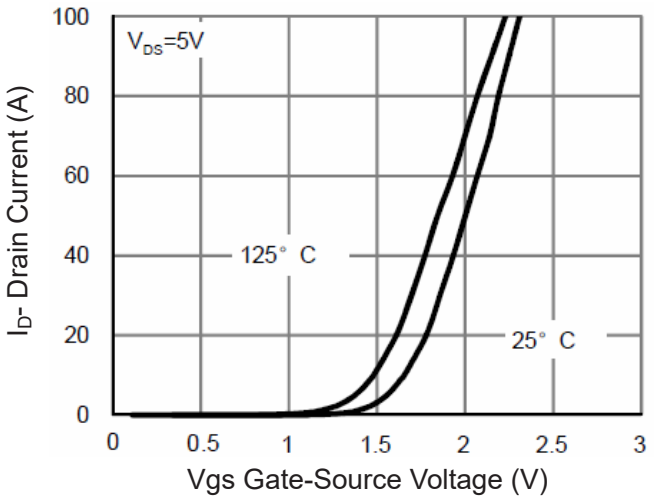


Figure 2 Transfer Characteristics

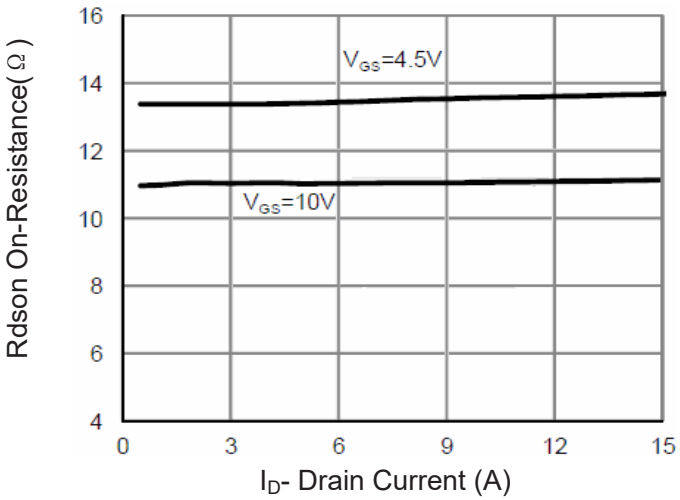


Figure 3 Rdson- Drain Current

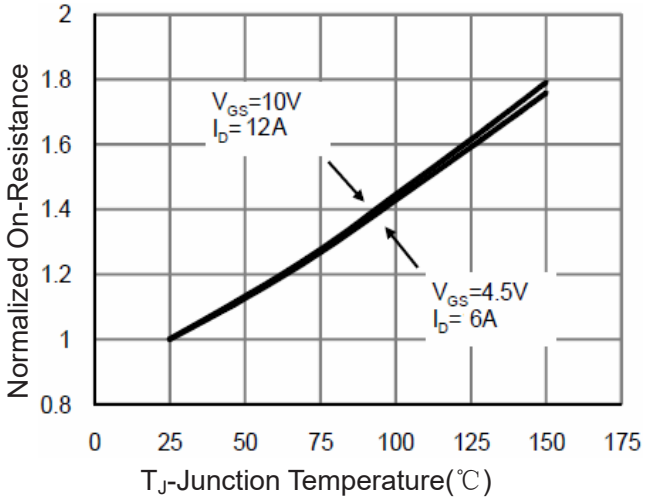


Figure 4 Rdson-JunctionTemperature

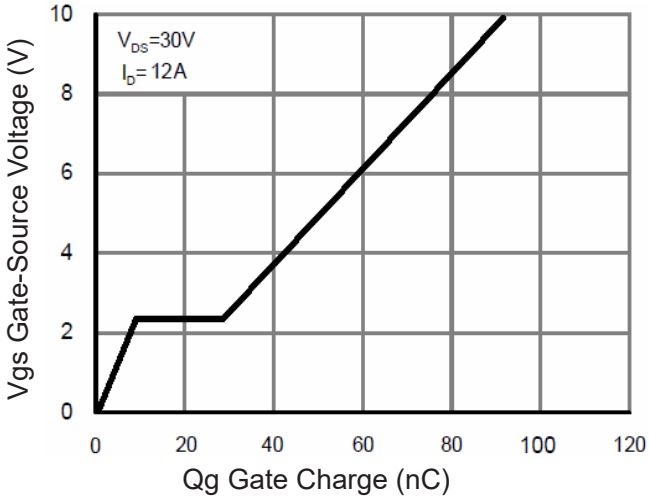


Figure 5 Gate Charge

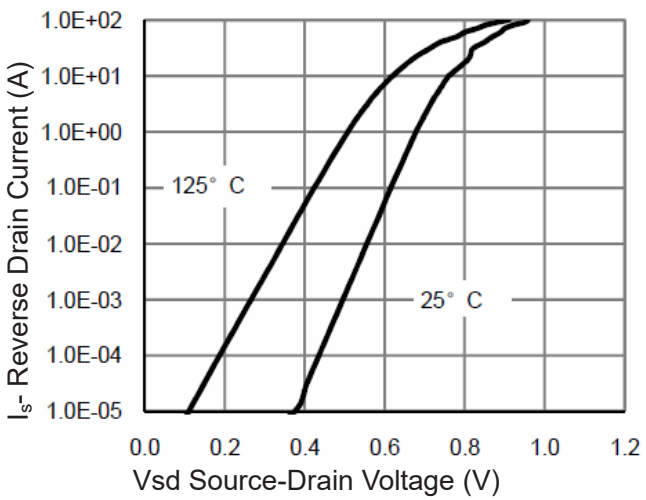


Figure 6 Source- Drain Diode Forward

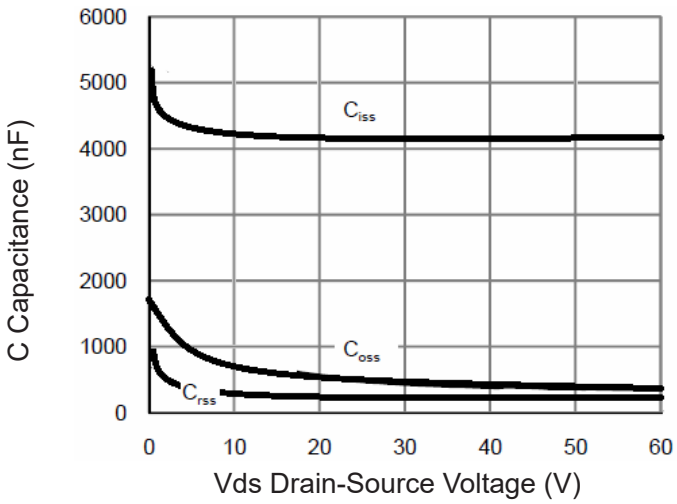


Figure 7 Capacitance vs Vds

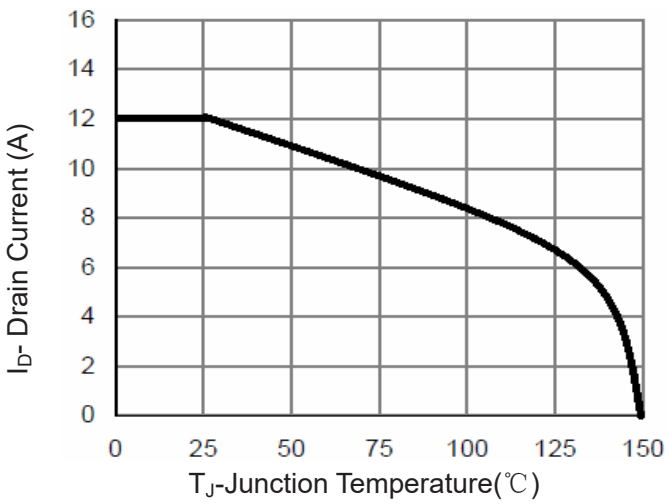


Figure 9 Current De-rating

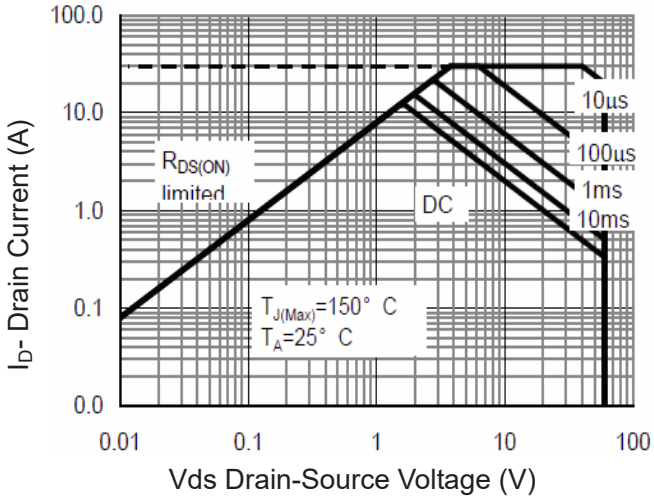


Figure 8 Safe Operation Area

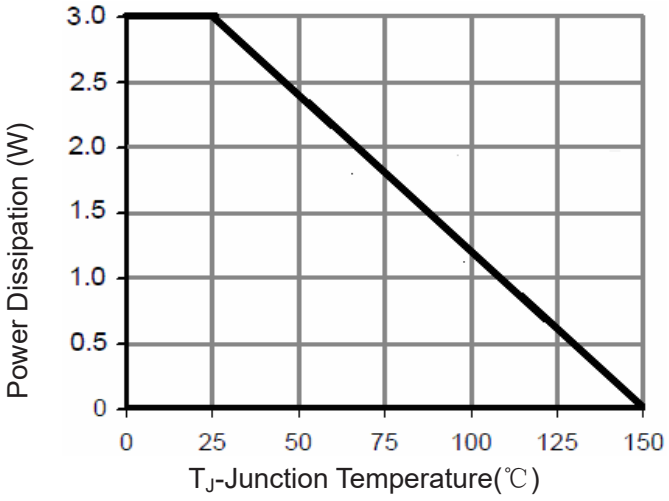


Figure 10 Power De-rating

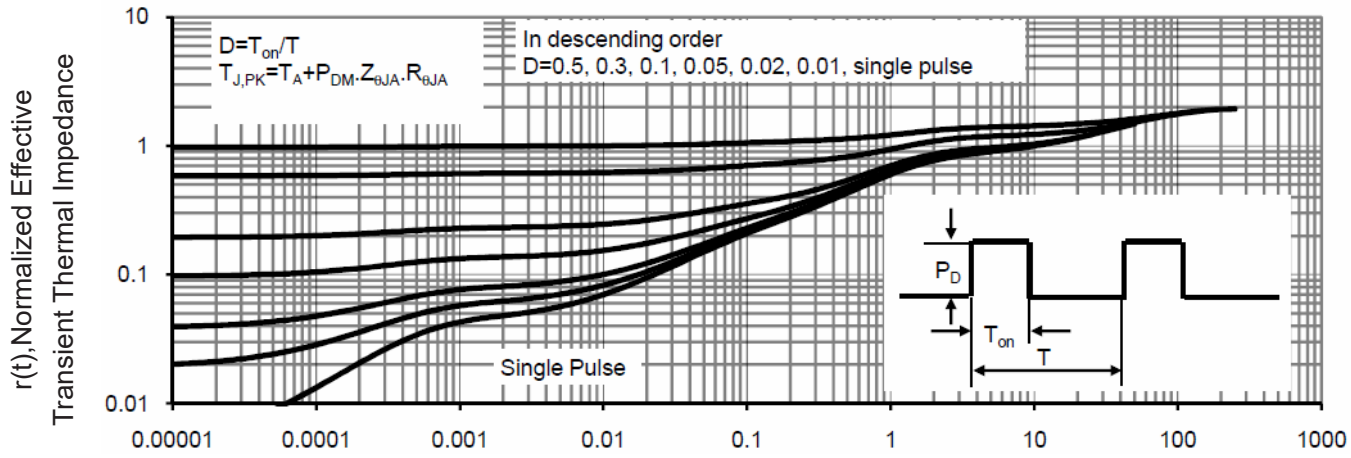
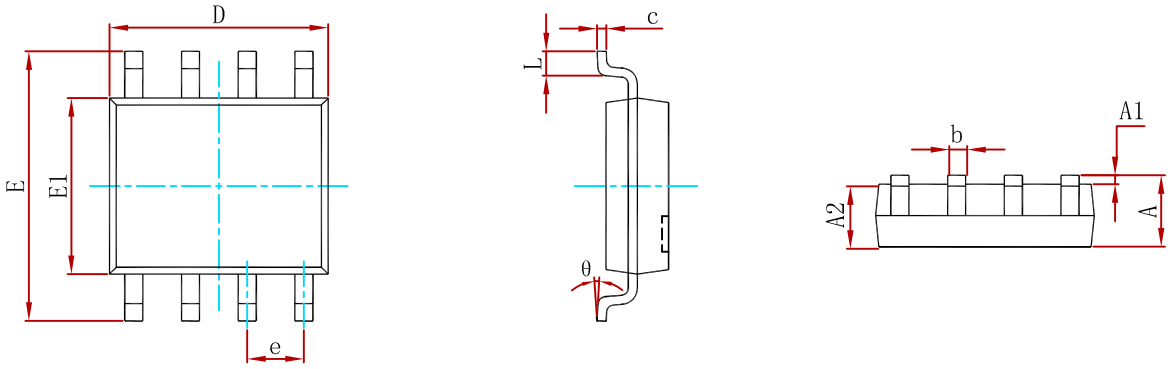


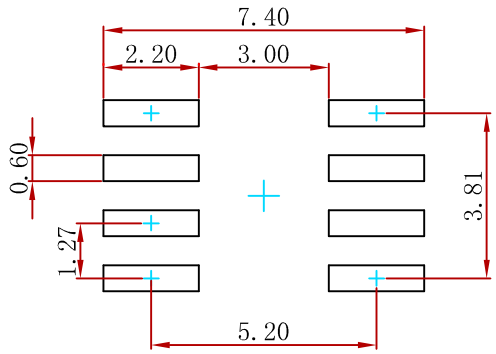
Figure 11 Normalized Maximum Transient Thermal Impedance

PACKAGEMECHANICALDATA



Symbol	DimensionsInMillimeters		DimensionsInInches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.007	0.010
D	4.800	5.000	0.189	0.197
e	1.270 (BSC)		0.050 (BSC)	
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:±0.05mm.
3.The pad layout is for reference purposes only.

REELSPECIFICATION

P/N	PKG	QTY
AO4266-MS	SOP-8	3000

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